



CZT31C NPN
CZT32C PNP

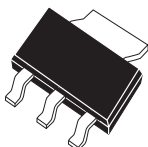
2.0W COMPLEMENTARY SILICON
POWER TRANSISTOR

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT31C and CZT32C types are surface mount epoxy molded complementary silicon transistors manufactured by the epitaxial base process, designed for surface mounted power amplifier applications up to 3.0 amps.

POWERTM
223



SOT-223 CASE

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

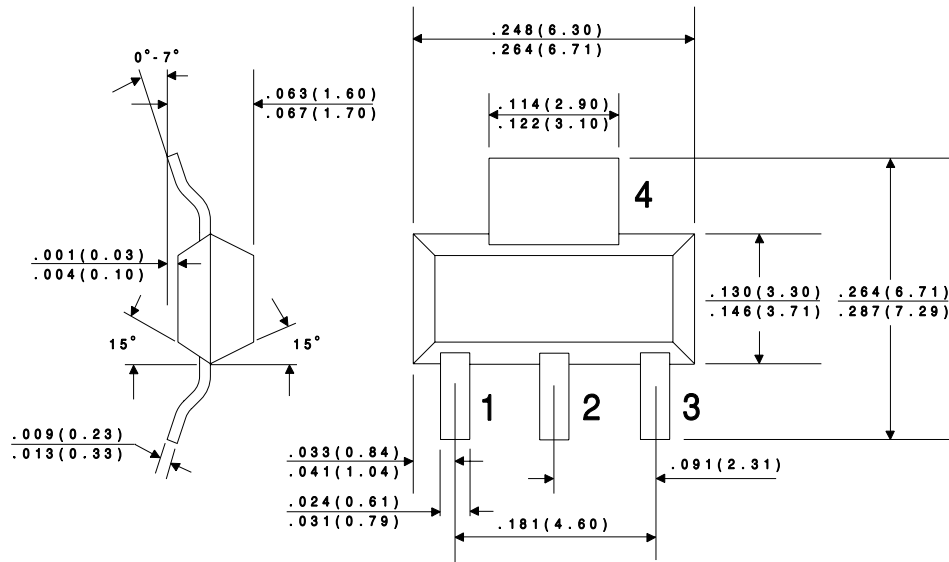
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	3.0	A
Peak Collector Current	I_{CM}	6.0	A
Base Current	I_B	1.0	A
Power Dissipation	P_D	2.0	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	62.5	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	$V_{CE}=100\text{V}$		200	μA
I_{CEO}	$V_{CE}=60\text{V}$		300	μA
I_{EBO}	$V_{EB}=5.0\text{V}$		1.0	mA
BV_{CEO}	$I_C=30\text{mA}$	100		V
* $V_{CE(SAT)}$	$I_C=3.0\text{A}, I_B=375\text{mA}$		1.2	V
* $V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=3.0\text{A}$		1.8	V
* h_{FE}	$V_{CE}=4.0\text{V}, I_C=1.0\text{A}$	25		
* h_{FE}	$V_{CE}=4.0\text{V}, I_C=3.0\text{A}$	10	100	
f_T	$V_{CE}=10\text{V}, I_C=500\text{mA}, f=1.0\text{MHz}$	3.0		MHz

* Pulsed, 2%D.C.

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR